

ORGANOMETALLIC PASTE**Patent number:** JP2003016837**Publication date:** 2003-01-17**Inventor:** SUGIURA TERUSADA; KAWAI AKINORI**Applicant:** NORITAKE CO LTD**Classification:****- International:** *H05K1/09; H01B1/20; H05K3/12; H05K1/09; H01B1/20; H05K3/12; (IPC1-7): H01B1/20; H05K1/09; H05K3/12***- european:****Application number:** JP20010198729 20010629**Priority number(s):** JP20010198729 20010629

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Abstract of JP2003016837

PROBLEM TO BE SOLVED: To provide an organometal paste, capable of forming a conductive film having the adhesive properties to a substrate highly balanced with an etching properties, and substantially containing no lead. **SOLUTION:** This organometallic paste of the present invention contains an organo-gold (Au) compound, an organo-rhodium (Rh) compound, and an organo-vanadium (V) compound in proportions of Au:10-50 wt.%, Rh:0.005-0.2 wt.%, and V:0.01-2.0 wt.%, in terms of elements respectively, and substantially contains no lead (Pd). The paste preferably contains 0.001-2.0 wt.% organo-bismuth (Bi) compound in terms of Bi element and/or 0.001-1.0 wt.% organo-silicon (Si) compound proportion in terms of Si element. The conductive film formed of the paste of the composition hereinbefore has superior balance between the adhesive properties to the substrate, and etching removability from the substrate.

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